

Attorney's Docket No. 5308-157IP2

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re: Das et al.

Confirmation No.: 3570

Serial No.: 10/045,542

Group Art Unit: 1762

Filed: October 26, 2001

Examiner: Michael. E. Barr

For: METHOD OF FABRICATING AN OXIDE LAYER ON A SILICON  
CARBIDE LAYER UTILIZING AN ANNEAL IN A HYDROGEN  
ENVIRONMENT

Date: February 04, 2004

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

**SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT UNDER 37**

**C.F.R. § 1.97(b)**

Sir:

Attached is a list of documents on form PTO-1449 together with copies of each identified document. This Information Disclosure Statement is submitted in accordance with 37 C.F.R. § 1.97(c), before final Office Action or Allowance, whichever is earlier.

No fee is believed due; however, the Commissioner is hereby authorized to charge any deficiency or credit any overpayment to Deposit Account No. 50 -0220.

Respectfully submitted,

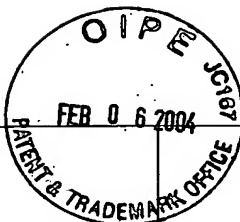
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I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to: Commissioner for Patents, PO Box 1450, Alexandria, VA 22313-1450 on February 04, 2004.

Ban Younan



**FORM PTO-1449** U.S. Department of Commerce  
Patent and Trademark Office

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**LIST OF DOCUMENTS CITED BY APPLICANT**

(Use several sheets if necessary)

Applicants: Das et al.

Filing Date: October 26, 2001

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**U. S. PATENT DOCUMENTS**

Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate

**FOREIGN PATENT DOCUMENTS**

		Document Number	Date	Country	Class	Subclass	Translation Yes   No

**OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)**

	1	Williams et al., "Passivation of the 4-H SiC/SiO <sub>2</sub> Interface with Nitric Oxide", <i>Materials Science Forum</i> , Vols. 389-393, 2002, pp. 967-972.
	2	Chung et al., "Effects of Anneals in Ammonia on the Interface Trap Density Near the Band Edges in 4H-Silicon Carbide Metal-Oxide-Semiconductor Capacitors", <i>Applied Physics Letters</i> , Vol. 77, No. 22, November 27, 2000, pp. 3601-3603.

EXAMINER  
\*EXAMINER

DATE CONSIDERED

Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.